Product data sheet

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- · Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV
- Very low Drain-Source on-state resistance  $R_{DSon}$  = 44  $m\Omega$

## 3. Applications

- Low-side load switch and charging switch for portable devices
- · Power management in battery-driven portables
- · LED driver
- · DC-to-DC converters

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.2	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 3.2 A; $T_j$ = 25 °C		-	44	67	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	4 3	G ← ↓ ↑
4	D	drain	2	T N
			Transparent top view DFN1010D-3 (SOT1215)	S 017aaa255

# 6. Ordering information

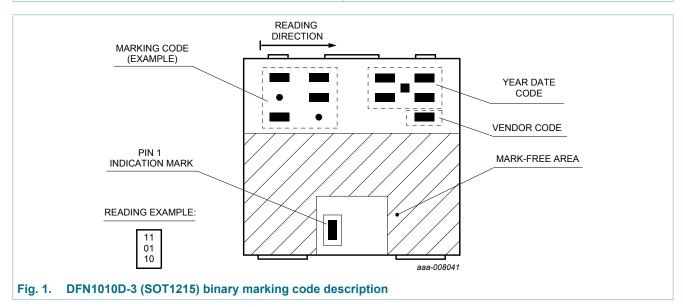
**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PMXB65ENE	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB65ENE	00 10 00



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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	3.2	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	12.8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	0.4	W
			[1]	-	1.07	W
		T <sub>sp</sub> = 25 °C		-	8.33	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode					'
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.9	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

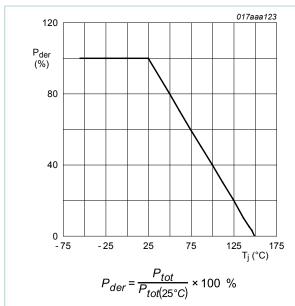
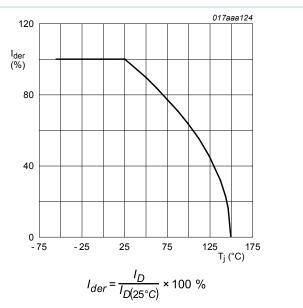


Fig. 2. Normalized total power dissipation as a function of junction temperature



ig. 3. Normalized continuous drain current as a function of junction temperature

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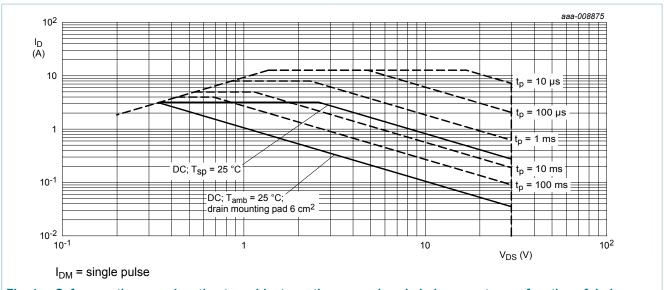


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	III II CC all	[1]	-	271	312	K/W
			[2]	-	102	117	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

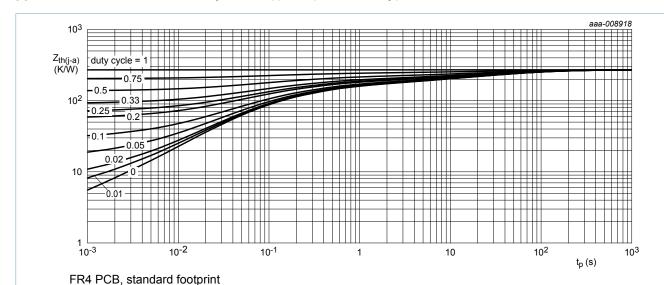


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

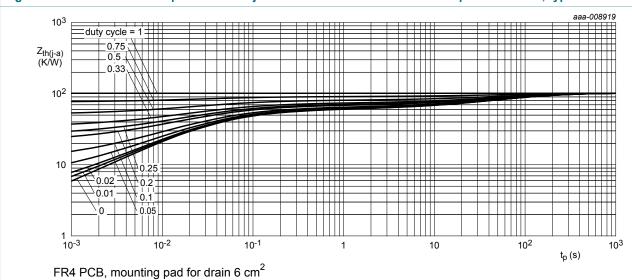


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara				. ) P	Мах	
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1	1.4	2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
R <sub>DSon</sub> drain-source resistance	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 3.2 A; $T_j$ = 25 °C	-	44	67	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3.2 A; T <sub>j</sub> = 150 °C	-	71	107	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2.9 A	-	56	79	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 3.2 A; $T_j$ = 25 °C	-	26	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	naracteristics				'	,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 3.2 A; $V_{GS}$ = 10 V;	-	6	11	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.7	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	295	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	40	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	31	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	12	-	ns
$t_{d(off)}$	turn-off delay time		-	11	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-dra	in diode		1			
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 0.9 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

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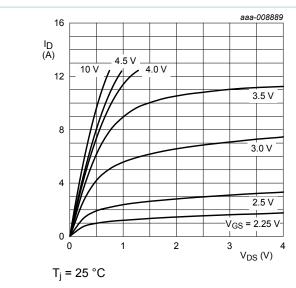


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

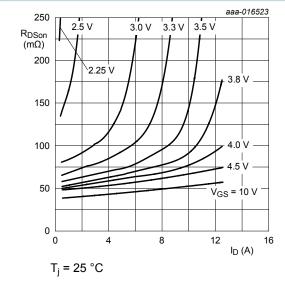


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

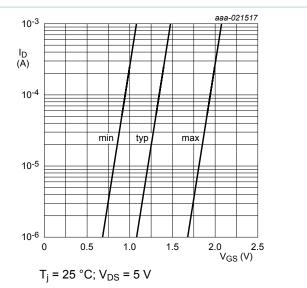


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

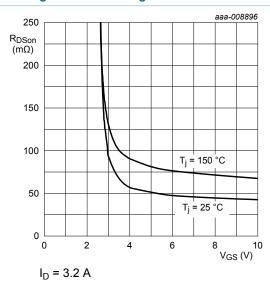


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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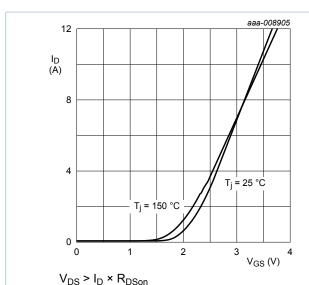


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

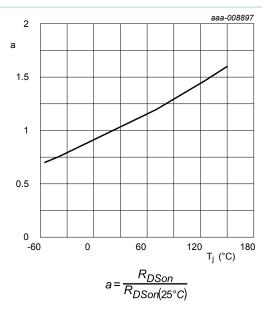


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

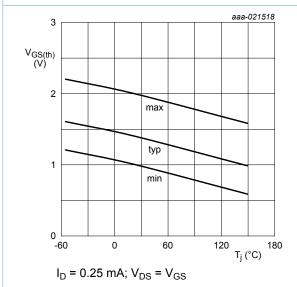


Fig. 13. Gate-source threshold voltage as a function of junction temperature

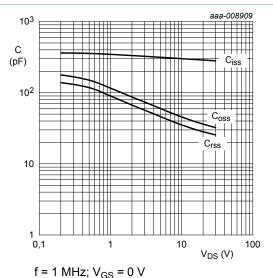
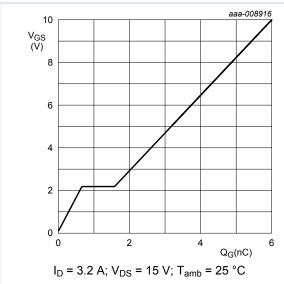


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub> Q<sub>GS2</sub>
Q<sub>G</sub>(tot)
017aaa137

Fig. 16. MOSFET transistor: Gate charge waveform definitions

Fig. 15. Gate-source voltage as a function of gate charge; typical values

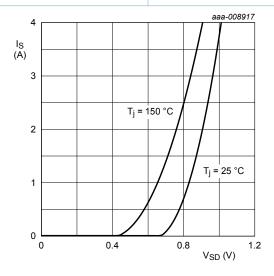
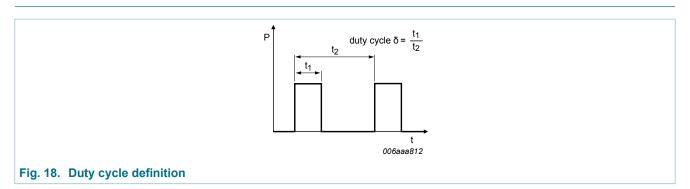


Fig. 17. Source current as a function of source-drain voltage; typical values

## 11. Test information

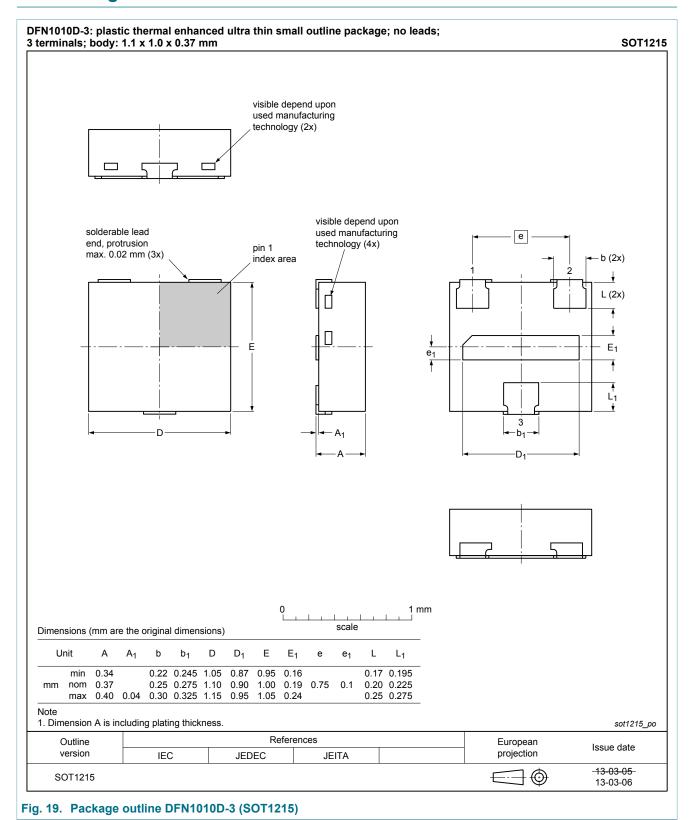
 $V_{GS} = 0 V$ 



PMXB65ENE

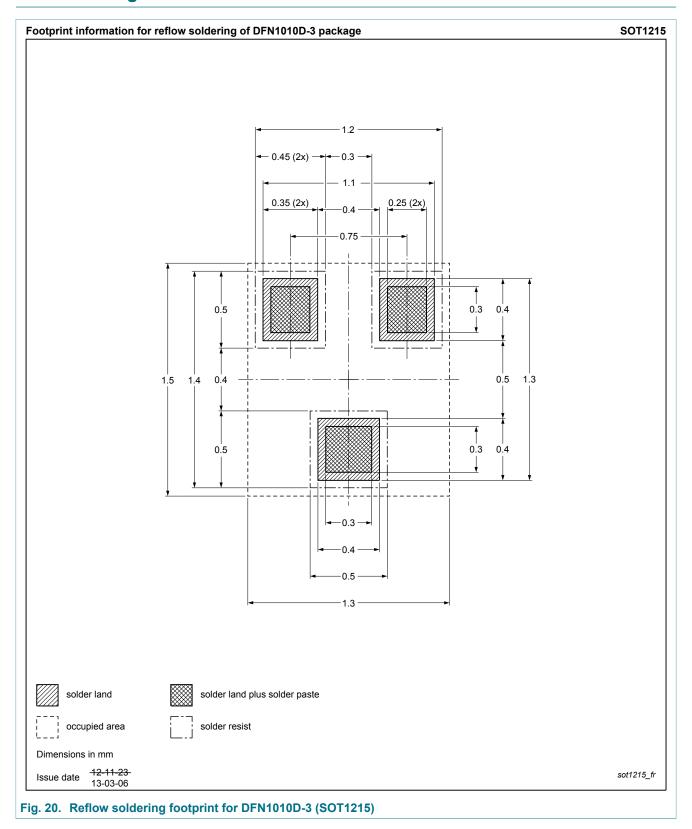
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## 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMXB65ENE v.4	20161103	Product data sheet	-	PMXB65ENE v.3				
Modifications:	Maximum value of g	Maximum value of gate-source threshold voltage revised						
PMXB65ENE v.3	20150520	Product data sheet	-	PMXB65ENE v.2				
PMXB65ENE v.2	20130924	Product data sheet	-	PMXB65ENE v.1				
PMXB65ENE v.1	20130910	Product data sheet	-	-				

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# 15. Legal information

#### **Data sheet status**

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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